

SMD Type

Diodes

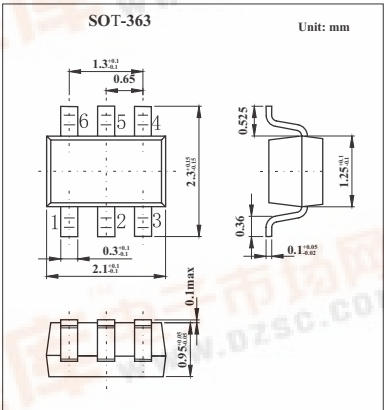
Dual Schottky Barrier Diodes

MBD110DWT1

MBD330DWT1;MBD770DWT1

■ Features

- Extremely Low Minority Carrier Lifetime
- Very Low Capacitance
- Low Reverse Leakage



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Reverse Voltage	VR	7	Vdc
		30	
		70	
Forward Power Dissipation TA = 25℃	PF	120	mA
Junction Temperature	TJ	-55 to +125	℃
Storage Temperature Range	Tstg	-55 to +150	℃

MBD110DWT1 MBD330DWT1;MBD770DWT1

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit	
Reverse Breakdown Voltage	MBD110DWT1 MBD330DWT1 MBD770DWT1	V _{BR(R)}	I _R = 10 μ A	7.0	10	Volts	
				30			
				70			
Diode Capacitance	MBD110DWT1	C _T	V _R = 0, f = 1.0 MHz		0.88	1.0	pF
Total Capacitance	MBD330DWT1	C _T	V _R = 15 Volts, f = 1.0 MHz		0.9	1.5	pF
	MBD770DWT1		V _R = 20 Volts, f = 1.0 MHz		0.5	1.0	
Reverse Leakage	MBD110DWT1	I _R	V _R = 3.0 V		0.02	0.25	μ A
	MBD330DWT1		V _R = 25 V		13	200	nAdc
	MBD770DWT1		V _R = 35 V		9	200	nAdc
Noise Figure	MBD110DWT1	NF	f = 1.0 GHz		6		dB
Forward Voltage	MBD110DWT1	V _F	I _F = 10 mA		0.5	0.6	Vdc
	MBD330DWT1		I _F = 1.0 mAdc		0.38	0.45	
	MBD770DWT1		I _F = 10 mA		0.52	0.6	
			I _F = 1.0 mAdc		0.47	0.5	
			I _F = 10 mA		0.7	1.0	

■ Marking

Type	MBD110DWT1	MMBD330DWT1	MBD770DWT1
Marking	M4	T4	H5